

App. No. 10/501,791
Reply dated August 29, 2005 to
"Notice of Non-Compliant Amendment"

Amendments to the Specification (other than claims):

Please replace the current title with the following amended title:

**CERAMICS HEATER CERAMIC SUSCEPTOR FOR SEMICONDUCTOR
PRODUCTION SYSTEM MANUFACTURING EQUIPMENT**

Please replace the paragraph beginning at page 9, line 2, with the following rewritten paragraph:

A paste of Y_2O_3 adhesive agent kneaded with a binder was print-coated on the surface of the remaining AlN substrate, which was then degreased at 500°C. The adhesive layer of this AlN substrate was then overlaid on the side of the AlN substrate on which the resistive heating element was formed, and the substrates were bonded by heating at 800°C. Sample ceramic susceptors having the Fig. [[1]] 2 configuration and differing in inter-line separation L and sectional smallest angle θ as set forth in the following Table I were thus produced.

Please replace the paragraph beginning at page 11, line 17, with the following rewritten paragraph:

A paste of SiO_2 adhesive agent kneaded with binder was print-coated on the surface of the other Si_3N_4 substrate, which was then degreased at 500°C. The adhesive layer of this Si_3N_4 substrate was then overlaid on the side of the Si_3N_4 substrate on which the resistive heating element was formed, and the substrates were bonded by heating at 800°C. Sample ceramic susceptors having the Fig. [1] 2 configuration and differing in inter-line separation L and sectional smallest angle θ as set forth in the following Table II were thus produced.

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Please replace the paragraph beginning at page 14, line 3, with the following rewritten paragraph:

A paste of SiO_2 adhesive agent kneaded with a binder was print-coated on the surface of the other AlON substrate, which was then degreased at 500°C. The adhesive layer of this AlON substrate was then overlaid on the side of the AlON substrate on which the resistive heating element was formed, and the substrates were bonded by heating at 800°C. Sample ceramic susceptors having the Fig. [[1]] 2 configuration and differing in inter-line separation L and sectional smallest angle θ as set forth in the following Table III were thus produced.

Please replace the paragraph beginning at page 19, line 3, with the following rewritten paragraph:

The resulting laminates were degreased for 5 hours at 600°C in a non-oxidizing atmosphere, then hot-pressed at 1800°C while applying pressure of 100 to 150 kg/cm², thereby producing 3 mm thick AlN plates. These plates were then cut to form 380-mm diameter disks, and the periphery of each disk was polished to a 300 mm diameter. Sample ceramic susceptors having the Fig. [[2]] 3 configuration internal featuring a tungsten resistive heating element and plasma electrode and differing in inter-line separation L and sectional smallest angle θ as set forth in the following Table V were thus produced.